Antidoping in Insulators and Semiconductors Having Intermediate Bands with Trapped Carriers

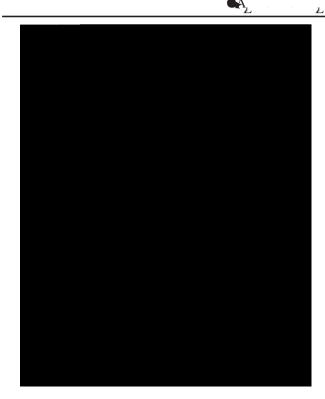
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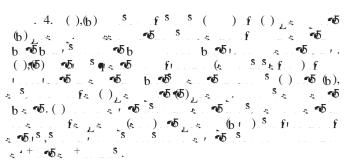
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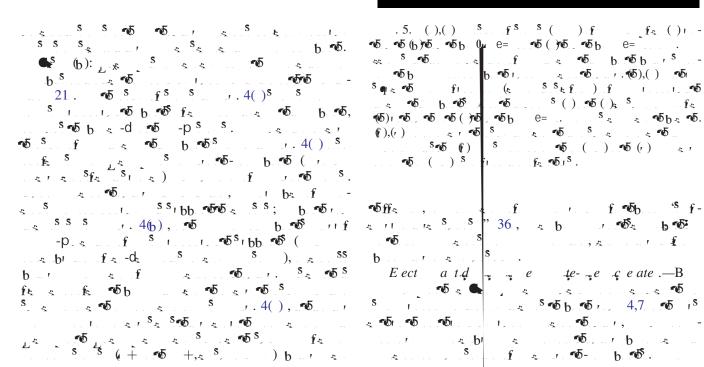
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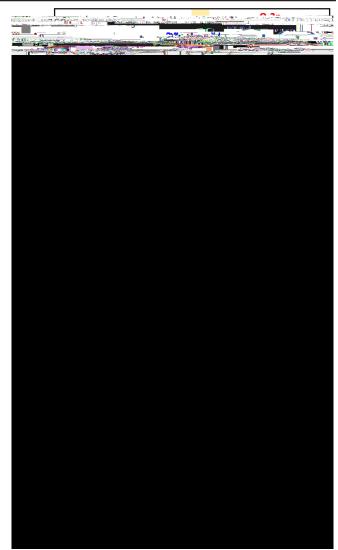
³Ce t de Ce ca Nat a e Hm a a , U , e dade Fede a d ABC, Sa t A de, Sa Pa 09210-80, B a ,

(. . . • 7 · . 2018; . · b . • • 11 . . . 2019)









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- s . . . B **97**, 075103 (2018).
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